

# Interference Search History print out NT

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(memory and vertical near transistors and trench near capacitors and diffusion near barrier and ring near shaped near insulator and deep near trench).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/10/27 10:12